

Errata

Corrections to “Low-Forward-Voltage-Drop 4H-SiC BJTs Without Base Contact Implantation”

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In [1], Dr. Lee’s photograph was incorrect. The corrected photograph appears below. We apologize for the error.



Hyung-Seok Lee (S’03–M’08) received the B.S. and M.S. degrees in electrical engineering from Korea University, Seoul, Korea, in 2000 and 2002, respectively, and the Tech. Lic. and Ph.D. degrees from the Royal Institute of Technology (KTH), Stockholm, Sweden, in 2005 and 2008, respectively.

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REFERENCES

- [1] H.-S. Lee, M. Domeij, C.-M. Zetterling, and M. Östling, “Low-forward-voltage-drop 4H-SiC BJTs without base contact implantation,” *IEEE Trans. Electron Devices*, vol. 55, no. 8, pp. 1907–1911, Aug. 2008.